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	APPLICANT MARTIN, T. et al.	
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U.S. PATENT DOCUMENTS

FOREIGN PATENT DOCUMENTS

OTHER DOCUMENTS (including Author, Title, Date, Pertinent pages, etc.)

MA MA	<p>Tsang; "Selective Area Growth of GaAs and $In_{0.53}Ga_{0.47}As$ Epilayer Structures by Chemical Beam Epitaxy Using Silicon Shadow Masks: A Demonstration of the Beam Nature", <i>Appl. Phys. Lett.</i> 46(8), 15 April 1985, pages 742-744.</p> <p>Tsang, "Chemical Beam Epitaxy of InP and GaAs", <i>Appl. Phys. Lett.</i> 45(11), 1 December 1984, pages 1234-1236.</p>

*Examiner

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116/05

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